

ABSTRACT

A semiconductor device equipped with a buried type capacitor directly buried inside a semiconductor substrate, wherein three-dimensional cavities 11 each having an aperture on the front side of the flat semiconductor substrate 10 are formed aligned with each other on the substrate 10, a capacitor part A is provided by implementing a capacitor structure of a substrate-buried type inside the cavity 11, and semiconductor base bodies 101 include these capacitor parts A, is provided.

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